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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Active
Core Processor	PowerPC e500v2
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	800MHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 90°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8533evtanga
Supplier Device Package Purchase URL	783-FCPBGA (29x29) https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8533evtanga

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NP

MPC8533E Overview

- Double-precision floating-point APU. Provides an instruction set for double-precision (64-bit) floating-point instructions that use the 64-bit GPRs.
- 36-bit real addressing
- Embedded vector and scalar single-precision floating-point APUs. Provide an instruction set for single-precision (32-bit) floating-point instructions.
- Memory management unit (MMU). Especially designed for embedded applications. Supports 4-Kbyte–4-Gbyte page sizes.
- Enhanced hardware and software debug support
- Performance monitor facility that is similar to, but separate from, the device performance monitor

The e500 defines features that are not implemented on this device. It also generally defines some features that this device implements more specifically. An understanding of these differences can be critical to ensure proper operations.

- 256-Kbyte L2 cache/SRAM
 - Flexible configuration
 - Full ECC support on 64-bit boundary in both cache and SRAM modes
 - Cache mode supports instruction caching, data caching, or both.
 - External masters can force data to be allocated into the cache through programmed memory ranges or special transaction types (stashing).
 - 1, 2, or 4 ways can be configured for stashing only.
 - Eight-way set-associative cache organization (32-byte cache lines)
 - Supports locking entire cache or selected lines. Individual line locks are set and cleared through Book E instructions or by externally mastered transactions.
 - Global locking and flash clearing done through writes to L2 configuration registers
 - Instruction and data locks can be flash cleared separately.
 - SRAM features include the following:
 - I/O devices access SRAM regions by marking transactions as snoopable (global).
 - Regions can reside at any aligned location in the memory map.
 - Byte-accessible ECC is protected using read-modify-write transaction accesses for smaller-than-cache-line accesses.
- Address translation and mapping unit (ATMU)
 - Eight local access windows define mapping within local 36-bit address space.
 - Inbound and outbound ATMUs map to larger external address spaces.
 - Three inbound windows plus a configuration window on PCI and PCI Express
 - Four outbound windows plus default translation for PCI and PCI Express
- DDR/DDR2 memory controller
 - Programmable timing supporting DDR and DDR2 SDRAM
 - 64-bit data interface



MPC8533E Overview

- Broadcast address (accept/reject)
- Hash table match on up to 512 multicast addresses
- Promiscuous mode
- Buffer descriptors backward compatible with MPC8260 and MPC860T 10/100 Ethernet programming models
- RMON statistics support
- 10-Kbyte internal transmit and 2-Kbyte receive FIFOs
- MII management interface for control and status
- Ability to force allocation of header information and buffer descriptors into L2 cache
- OCeaN switch fabric
 - Full crossbar packet switch
 - Reorders packets from a source based on priorities
 - Reorders packets to bypass blocked packets
 - Implements starvation avoidance algorithms
 - Supports packets with payloads of up to 256 bytes
- Integrated DMA controller
 - Four-channel controller
 - All channels accessible by both the local and remote masters
 - Extended DMA functions (advanced chaining and striding capability)
 - Support for scatter and gather transfers
 - Misaligned transfer capability
 - Interrupt on completed segment, link, list, and error
 - Supports transfers to or from any local memory or I/O port
 - Selectable hardware-enforced coherency (snoop/no snoop)
 - Ability to start and flow control each DMA channel from external 3-pin interface
 - Ability to launch DMA from single write transaction
- PCI controller
 - PCI 2.2 compatible
 - One 32-bit PCI port with support for speeds from 16 to 66 MHz
 - Host and agent mode support
 - 64-bit dual address cycle (DAC) support
 - Supports PCI-to-memory and memory-to-PCI streaming
 - Memory prefetching of PCI read accesses
 - Supports posting of processor-to-PCI and PCI-to-memory writes
 - PCI 3.3-V compatible
 - Selectable hardware-enforced coherency



DDR and DDR2 SDRAM

Table 16 provides the input AC timing specifications for the DDR SDRAM when $GV_{DD}(typ) = 2.5 V$.

Table 16. DDR SDRAM Input AC Timing Specifications for 2.5-V Interface

At recommended operating conditions.

Parameter	Symbol	Min	Мах	Unit	Notes
AC input low voltage	V _{IL}	—	MV _{REF} – 0.31	V	—
AC input high voltage	V _{IH}	MV _{REF} + 0.31	—	V	—

Table 17 provides the input AC timing specifications for the DDR SDRAM interface.

Table 17. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol	Min	Мах	Unit	Notes
Controller skew for MDQS—MDQ/MECC/MDM	t _{CISKEW}			ps	1, 2
533 MHz		-300	300		3
400 MHz		-365	365		—
333 MHz		-390	390		_

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that will be captured with MDQS[n]. This should be subtracted from the total timing budget.

- 2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW} . This can be determined by the following equation: $t_{DISKEW} = \pm (T/4 abs(t_{CISKEW}))$, where T is the clock period and $abs(t_{CISKEW})$ is the absolute value of t_{CISKEW} . See Figure 3.
- 3. Maximum DDR1 frequency is 400 MHz.

Figure 3 shows the DDR SDRAM input timing diagram.



Figure 3. DDR SDRAM Input Timing Diagram (t_{DISKEW})



DDR and DDR2 SDRAM

6.2.2 DDR SDRAM Output AC Timing Specifications

Table 18 provides the output AC timing specifications for the DDR SDRAM interface.

Table 18. DDR SDRAM Output AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol ¹	Min	Max	Unit	Notes
MCK[n] cycle time, MCK[n]/MCK[n] crossing	t _{MCK}	3.75	6	ns	2
ADDR/CMD output setup with respect to MCK	t _{DDKHAS}			ns	3
533 MHz 400 MHz 333 MHz		1.48 1.95 2.40	 		7
ADDR/CMD output hold with respect to MCK	t _{DDKHAX}			ns	3
533 MHz 400 MHz 333 MHz		1.48 1.95 2.40			7
MCS[n] output setup with respect to MCK	t _{DDKHCS}			ns	3
533 MHz 400 MHz 333 MHz		1.48 1.95 2.40			7
MCS[n] output hold with respect to MCK	t _{DDKHCX}			ns	3
533 MHz 400 MHz 333 MHz		1.48 1.95 2.40			7
MCK to MDQS Skew	t _{DDKHMH}	-0.6	0.6	ns	4
MDQ/MECC/MDM output setup with respect to MDQS	^t DDKHDS, t _{DDKLDS}			ps	5
533 MHz 400 MHz 333 MHz		538 700 900			7
MDQ/MECC/MDM output hold with respect to MDQS	t _{DDKHDX,} t _{DDKLDX}			ps	5
533 MHz 400 MHz 333 MHz		538 700 900			7 — —
MDQS preamble	t _{DDKHMP}	0.75 x tMCK	—	ns	6



Enhanced Three-Speed Ethernet (eTSEC), MII Management

Table 32. RGMII and RTBI AC Timing Specifications (continued)

At recommended operating conditions with L/TV_{DD} of 2.5 V \pm 5%.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit	Notes
Fall time (20%-80%)	t _{RGTF}			0.75	ns	—

Notes:

- In general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).
- 2. This implies that PC board design will require clocks to be routed such that an additional trace delay of greater than 1.5 ns will be added to the associated clock signal.
- 3. For 10 and 100 Mbps, t_{BGT} scales to 400 ns ± 40 ns and 40 ns ± 4 ns, respectively.
- 4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned between.
- 5. Guaranteed by design.

Figure 18 shows the RGMII and RTBI AC timing and multiplexing diagrams.



Figure 18. RGMII and RTBI AC Timing and Multiplexing Diagrams



Table 42. Local Bus General Ti	ing Parameters (BV _{DD} =	1.8 V DC) (continued)
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Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus clock to output high impedance for LAD/LDP	t _{LBKHOZ2}	_	2.6	ns	5

Notes:

- The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{LBIXKH1} symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
 </sub>
- 2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.

3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 1.8-V signaling levels.

- 4. Input timings are measured at the pin.
- 5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
- 7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at BV_{DD}/2.

Figure 23 provides the AC test load for the local bus.



Figure 23. Local Bus AC Test Load



Local Bus



Figure 25. Local Bus Signals (PLL Bypass Mode)

NOTE

In PLL bypass mode, LCLK[n] is the inverted version of the internal clock with the delay of t_{LBKHKT} . In this mode, signals are launched at the rising edge of the internal clock and are captured at falling edge of the internal clock withe the exception of LGTA/LUPWAIT (which is captured on the rising edge of the internal clock).







Figure 27. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (PLL Bypass Mode)



Figure 34 provides the AC test load for the I^2C .



Figure 34. I²C AC Test Load

Figure 35 shows the AC timing diagram for the I^2C bus.



Figure 35. I²C Bus AC Timing Diagram

14 GPIO

This section describes the DC and AC electrical specifications for the GPIO interface of the MPC8533E.

14.1 GPIO DC Electrical Characteristics

Table 48 provides the DC electrical characteristics for the GPIO interface.

Parameter	Symbol	Min	Мах	Unit	Notes
High-level input voltage	V _{IH}	2	OV _{DD} + 0.3	V	
Low-level input voltage	V _{IL}	-0.3	0.8	V	
Input current ($V_{IN} = 0 V \text{ or } V_{IN} = V_{DD}$)	I _{IN}	—	±5	μA	1
High-level output voltage ($OV_{DD} = mn$, $I_{OH} = -2 mA$)	V _{OH}	2.4	—	V	
Low-level output voltage ($OV_{DD} = min, I_{OL} = 2 mA$)	V _{OL}	—	0.4	V	_

Note:

1. Note that the symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

High-Speed Serial Interfaces (HSSI)

- For external DC-coupled connection, as described in Section 16.2.1, "SerDes Reference Clock Receiver Characteristics," the maximum average current requirements sets the requirement for average voltage (common mode voltage) to be between 100 and 400 mV.
 Figure 42 shows the SerDes reference clock input requirement for DC-coupled connection scheme.
- For external AC-coupled connection, there is no common mode voltage requirement for the clock driver. Since the external AC-coupling capacitor blocks the DC level, the clock driver and the SerDes reference clock receiver operate in different command mode voltages. The SerDes reference clock receiver in this connection scheme has its common mode voltage set to SGND_SRDSn. Each signal wire of the differential inputs is allowed to swing below and above the command mode voltage (SGND_SRDSn). Figure 43 shows the SerDes reference clock input requirement for AC-coupled connection scheme.
- Single-ended Mode
 - The reference clock can also be single-ended. The SDn_REF_CLK input amplitude (single-ended swing) must be between 400 and 800 mV peak-peak (from Vmin to Vmax) with SDn_REF_CLK either left unconnected or tied to ground.
 - The SDn_REF_CLK input average voltage must be between 200 and 400 mV. Figure 44 shows the SerDes reference clock input requirement for single-ended signaling mode.
 - To meet the input amplitude requirement, the reference clock inputs might need to be DC or AC-coupled externally. For the best noise performance, the reference of the clock could be DC or AC-coupled into the unused phase (SDn_REF_CLK) through the same source impedance as the clock input (SDn_REF_CLK) in use.





High-Speed Serial Interfaces (HSSI)

16.2.4 AC Requirements for SerDes Reference Clocks

The clock driver selected should provide a high quality reference clock with low phase noise and cycle-to-cycle jitter. Phase noise less than 100 kHz can be tracked by the PLL and data recovery loops and is less of a problem. Phase noise above 15 MHz is filtered by the PLL. The most problematic phase noise occurs in the 1–15 MHz range. The source impedance of the clock driver should be 50 Ω to match the transmission line and reduce reflections which are a source of noise to the system.

Table 52 describes some AC parameters common to SGMII, and PCI Express protocols.

Parameter	Symbol	Min	Max	Unit	Notes
Rising Edge Rate	Rise Edge Rate	1.0	4.0	V/ns	2, 3
Falling Edge Rate	Fall Edge Rate	1.0	4.0	V/ns	2, 3
Differential Input High Voltage	V _{IH}	+200		mV	2
Differential Input Low Voltage	V _{IL}	_	-200	mV	2
Rising edge rate (SD <i>n</i> _REF_CLK) to falling edge rate (SD <i>n</i> _REF_CLK) matching	Rise-Fall Matching	_	20	%	1, 4

Table 52. SerDes Reference Clock Common AC Parameters

Notes:

- 1. Measurement taken from single ended waveform.
- 2. Measurement taken from differential waveform.
- 3. Measured from –200 mV to +200 mV on the differential waveform (derived from SD*n*_REF_CLK minus SD*n*_REF_CLK). The signal must be monotonic through the measurement region for rise and fall time. The 400 mV measurement window is centered on the differential zero crossing. See Figure 49.
- 4. Matching applies to rising edge rate for SDn_REF_CLK and falling edge rate for SDn_REF_CLK. It is measured using a 200 mV window centered on the median cross point where SDn_REF_CLK rising meets SDn_REF_CLK falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations. The rise edge rate of SDn_REF_CLK should be compared to the fall edge rate of SDn_REF_CLK, the maximum allowed difference should not exceed 20% of the slowest edge rate. See Figure 50.



Figure 49. Differential Measurement Points for Rise and Fall Time



PCI Express

Symbol	Parameter	Min	Nom	Max	Unit	Comments
V _{TX-RCV-DETECT}	Amount of voltage change allowed during receiver detection		_	600	mV	The total amount of voltage change that a transmitter can apply to sense whether a low impedance receiver is present. See Note 6.
V _{TX-DC-CM}	TX DC common mode voltage	0	_	3.6	V	The allowed DC common mode voltage under any conditions. See Note 6.
I _{TX-SHORT}	TX short circuit current limit	—	_	90	mA	The total current the transmitter can provide when shorted to its ground.
T _{TX-IDLE-MIN}	Minimum time spent in electrical idle	50			UI	Minimum time a transmitter must be in electrical idle utilized by the receiver to start looking for an electrical idle exit after successfully receiving an electrical idle ordered set.
T _{TX-IDLE-SET-TO-IDLE}	Maximum time to transition to a valid electrical idle after sending an electrical Idle ordered set	_		20	UI	After sending an electrical idle ordered set, the transmitter must meet all electrical idle specifications within this time. This is considered a debounce time for the transmitter to meet electrical idle after transitioning from LO.
T _{TX-IDLE} -TO-DIFF-DATA	Maximum time to transition to valid TX specifications after leaving an electrical idle condition			20	UI	Maximum time to meet all TX specifications when transitioning from electrical idle to sending differential data. This is considered a debounce time for the TX to meet all TX specifications after leaving electrical idle.
RL _{TX-DIFF}	Differential return loss	12	_	_	dB	Measured over 50 MHz to 1.25 GHz. See Note 4.
RL _{TX-CM}	Common mode return loss	6	_	_	dB	Measured over 50 MHz to 1.25 GHz. See Note 4.
Z _{TX-DIFF-DC}	DC differential TX impedance	80	100	120	Ω	TX DC differential mode low impedance.
Z _{TX-DC}	Transmitter DC impedance	40	_	_	Ω	Required TX D+ as well as D– DC Impedance during all states.
L _{TX-SKEW}	Lane-to-lane output skew	_		500 + 2 UI	ps	Static skew between any two transmitter lanes within a single link.
C _{TX}	AC coupling capacitor	75	_	200	nF	All transmitters shall be AC coupled. The AC coupling is required either within the media or within the transmitting component itself.

Table 54. Differential Transmitter (TX) Output Specifications (continued)



18 Package Description

This section details package parameters, pin assignments, and dimensions.

18.1 Package Parameters for the MPC8533E FC-PBGA

The package parameters for flip chip plastic ball grid array (FC-PBGA) are provided in Table 56.

Parameter	PBGA ¹
Package outline	29 mm × 29 mm
Interconnects	783
Ball pitch	1 mm
Ball diameter (typical)	0.6 mm
Solder ball (Pb-free)	96.5% Sn 3.5% Ag

Table 56. Package Parameters

Note:

1. (FC-PBGA) without a lid.



18.3 Pinout Listings

Table 57 provides the pinout listing for the MPC8533E 783 FC-PBGA package.

NOTE

The naming convention of TSEC1 and TSEC3 is used to allow the splitting voltage rails for the eTSEC blocks and to ease the port of existing PowerQUICC III software.

NOTE

The DMA_DACK[0:1] and TEST_SEL pins must be set to a proper state during POR configuration. Please refer to Table 57 for more details.

Signal	Package Pin Number	Pin Type	Power Supply	Notes
	PCI			
PCI1_AD[31:0]	AE8, AD8, AF8, AH12, AG12, AB9, AC9, AE9, AD10, AE10, AC11, AB11, AB12, AC12, AF12, AE11, Y14, AE15, AC15, AB15, AA15, AD16, Y15, AB16, AF18, AE18, AC17, AE19, AD19, AB17, AB18, AA16	I/O	OV _{DD}	_
PCI1_C_BE[3:0]	AC10, AE12, AA14, AD17	I/O	OV _{DD}	_
PCI1_GNT[4:1]	AE7, AG11,AH11, AC8	0	OV _{DD}	4, 8, 24
PCI1_GNT0	AE6	I/O	OV _{DD}	—
PCI1_IRDY	AF13	I/O	OV _{DD}	2
PCI1_PAR	AB14	I/O	OV _{DD}	
PCI1_PERR	AE14	I/O	OV _{DD}	2
PCI1_SERR	AC14	I/O	OV _{DD}	2
PCI1_STOP	AA13	I/O	OV _{DD}	2
PCI1_TRDY	AD13	I/O	OV _{DD}	2
PCI1_REQ[4:1]	AF9, AG10, AH10, AD6	I	OV _{DD}	—
PCI1_REQ0	AB8	I/O	OV _{DD}	—
PCI1_CLK	AH26	I	OV _{DD}	_
PCI1_DEVSEL	AC13	I/O	OV _{DD}	2
PCI1_FRAME	AD12	I/O	OV _{DD}	2
PCI1_IDSEL	AG6	ļ	OV _{DD}	—

Table 57. MPC8533E Pinout Listing



Signal	Package Pin Number	Pin Type	Power Supply	Notes
LCS6/DMA_DACK2	J16	0	BV _{DD}	1
LCS7/DMA_DDONE2	L18	0	BV _{DD}	1
LWE0/LBS0/LSDDQM[0]	J22	0	BV _{DD}	4, 8
LWE1/LBS1/LSDDQM[1]	H22	0	BV _{DD}	4, 8
LWE2/LBS2/LSDDQM[2]	H23	0	BV _{DD}	4, 8
LWE3/LBS3/LSDDQM[3]	H21	0	BV _{DD}	4, 8
LALE	J26	0	BV _{DD}	4, 7, 8
LBCTL	J25	0	BV _{DD}	4, 7, 8
LGPL0/LSDA10	J20	0	BV _{DD}	4, 8
LGPL1/LSDWE	К20	0	BV _{DD}	4, 8
LGPL2/LOE/LSDRAS	G20	0	BV _{DD}	4, 7, 8
LGPL3/LSDCAS	H18	0	BV _{DD}	4, 8
LGPL4/LGTA/LUPWAIT/ LPBSE	L20	I/O	BV _{DD}	28
LGPL5	K19	0	BV _{DD}	4, 8
LCKE	L17	0	BV _{DD}	—
LCLK[0:2]	H24, J24, H25	0	BV _{DD}	—
LSYNC_IN	D27	I	BV _{DD}	—
LSYNC_OUT	D28	0	BV _{DD}	—
	DMA			
DMA_DACK[0:1]	Y13, Y12	0	OV _{DD}	4, 8, 9
DMA_DREQ[0:1]	AA10, AA11	I	OV _{DD}	—
DMA_DDONE[0:1]	AA7, Y11	0	OV _{DD}	—
	Programmable Interrupt Contro	oller		
UDE	AH15	I	OV _{DD}	—
MCP	AG18	I	OV _{DD}	—
IRQ[0:7]	AG22, AF17, AD21, AF19, AG17, AF16, AC23, AC22	I	OV _{DD}	—
IRQ[8]	AC19	I	OV _{DD}	—
IRQ[9]/DMA_DREQ3	AG20	I	OV _{DD}	1
IRQ[10]/DMA_DACK3	AE27	I/O	OV _{DD}	1
IRQ[11]/DMA_DDONE3	AE24	I/O	OV _{DD}	1
IRQ_OUT	AD14	0	OV _{DD}	2

Table 57. MPC8533E Pinout Listing (continued)



Table 57. MPC8533E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes				
DFT								
L1_TSTCLK	AC20	I	OV _{DD}	18				
L2_TSTCLK	AE17	I	OV _{DD}	18				
LSSD_MODE	AH19	I	OV _{DD}	18				
TEST_SEL	AH13	I	OV _{DD}	3				
	Thermal Management	·						
TEMP_ANODE	Y3	—	_	13				
TEMP_CATHODE	ААЗ		—	13				
	Power Management			•				
ASLEEP	AH17	0	OV _{DD}	8, 15, 21				
	Power and Ground Signals							
GND	D5, M10, F4, D26, D23, C12, C15, E20, D8, B10, E3, J14, K21, F8, A3, F16, E12, E15, D17, L1, F21, H1, G13, G15, G18, C6, A14, A7, G25, H4, C20, J12, J15, J17, F27, M5, J27, K11, L26, K7, K8, L12, L15, M14, M16, M18, N13, N15, N17, N2, P5, P14, P16, P18, R13, R15, R17, T14, T16, T18, U13, U15, U17, AA8, U6, Y10, AC21, AA17, AC16, V4, AD7, AD18, AE23, AF11, AF14, AG23, AH9, A27, B28, C27		_					
OV _{DD} [1:17]	Y16, AB7, AB10, AB13, AC6, AC18, AD9, AD11, AE13, AD15, AD20, AE5, AE22, AF10, AF20, AF24, AF27	Power for PCI and other standards (3.3 V)	OV _{DD}	_				
LV _{DD} [1:2]	R4, U3	Power for TSEC1 interfaces (2.5 V, 3.3 V)	LV _{DD}	_				
TV _{DD} [1:2]	N8, R10	Power for TSEC3 interfaces (2.5 V, 3.3 V)	TV _{DD}	_				
GV _{DD}	B1, B11, C7, C9, C14, C17, D4, D6, R3, D15, E2, E8,C24, E18, F5, E14, C21, G3, G7, G9, G11, H5, H12, E22, F15, J10, K3, K12, K14, H14, D20, E11, M1, N5	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5 V)	GV _{DD}	_				
BV _{DD}	L23, J18, J19, F20, F23, H26, J21, J23	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV _{DD}	—				



Table 57	. MPC8533E	Pinout Listing	(continued)
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Signal	Package Pin Number	Pin Type	Power Supply	Notes
AVDD_SRDS	W28	Power for SRDSPLL (1.0 V)	_	19
AVDD_SRDS2	AG1	Power for SRDSPLL (1.0 V)	_	19
SENSEVDD	W11	0	V _{DD}	12
SENSEVSS	W10	_	—	12
	Analog Signals			
MVREF	A28	Reference voltage signal for DDR	MVREF	_
SD1_IMP_CAL_RX	M26	—	200 Ω to GND	_
SD1_IMP_CAL_TX	AE28	—	100 Ω to GND	_
SD1_PLL_TPA	V26	_	AVDD_SRDS ANALOG	17
SD2_IMP_CAL_RX	АНЗ	I	200 Ω to GND	_
SD2_IMP_CAL_TX	Y1	I	100 Ω to GND	_
SD2_PLL_TPA	AH1	0	AVDD_SRDS2 ANALOG	17
	No Connect Pins			
NC	C19, D7, D10, K13, L6, K9, B6, F12, J7, M19, M25, N19, N24, P19, R19, AB19, T12, W3, M12, W5, P12, T19, W1, W7, L13, U19, W4, V8, V9, V10, V11, V12, V13, V14, V15, V16, V17, V18, V19, W2, W6, W8, T11, U11, W12, W13, W14, W15, W16, W17, W18, W19, W27, V25, Y17, Y18, Y19, AA18, AA19, AB20, AB21, AB22, AB23, J9	_	_	_

Notes:

1.All multiplexed signals are listed only once and do not re-occur. For example, LCS5/DMA_REQ2 is listed only once in the Local Bus Controller Interface section, and is not mentioned in the DMA section even though the pin also functions as DMA_REQ2.

2.Recommend a weak pull-up resistor (2–10 K Ω) be placed on this pin to OV_{DD}.

3. This pin must always be pulled high.

4. This pin is a reset configuration pin. It has a weak internal pull-up P-FET which is enabled only when the processor is in the reset state. This pull-up is designed such that it can be overpowered by an external 4.7-kΩ pull-down resistor. However, if the signal is intended to be high after reset, and if there is any device on the net which might pull down the value of the net at reset, then a pull-up or active driver is needed.

5. Treat these pins as no connects (NC) unless using debug address functionality.



Clocking

19 Clocking

This section describes the PLL configuration of the MPC8533E. Note that the platform clock is identical to the core complex bus (CCB) clock.

19.1 Clock Ranges

Table 58 provides the clocking specifications for the processor cores and Table 59 provides the clocking specifications for the memory bus.

Characteristic	Maximum Processor Core Frequency 667 MHz 800 MHz 1000 MHz 1067 MHz					Unit	Notes			
	Min	Мах	Min	Max	Min	Max	Min	Мах		
e500 core processor frequency	667	667	667	800	667	1000	667	1067	MHz	1, 2

Table 58. Processor Core Clocking Specifications

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 19.2, "CCB/SYSCLK PLL Ratio," and Section 19.3, "e500 Core PLL Ratio," for ratio settings.

2. The minimum e500 core frequency is based on the minimum platform frequency of 333 MHz.

Table 59. Memory Bus Clocking Specifications

Characteristic	Maximum Processor Core Frequency 667, 800, 1000, 1067 MHz		Unit	Notes
	Min	Мах		
Memory bus clock speed	166	266	MHz	1, 2

Notes:

- 1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 19.2, "CCB/SYSCLK PLL Ratio," and Section 19.3, "e500 Core PLL Ratio," for ratio settings.
- 2. The memory bus speed is half of the DDR/DDR2 data rate, hence, half of the platform clock frequency.

19.2 CCB/SYSCLK PLL Ratio

The CCB clock is the clock that drives the e500 core complex bus (CCB), and is also called the platform clock. The frequency of the CCB is set using the following reset signals (see Table 60):

- SYSCLK input signal
- Binary value on LA[28:31] at power up



Note that there is no default for this PLL ratio; these signals must be pulled to the desired values. Also note that the DDR data rate is the determining factor in selecting the CCB bus frequency, since the CCB frequency must equal the DDR data rate.

Binary Value of LA[28:31] Signals	CCB:SYSCLK Ratio	Binary Value of LA[28:31] Signals	CCB:SYSCLK Ratio
0000	16:1	1000	8:1
0001	Reserved	1001	9:1
0010	Reserved	1010	10:1
0011	3:1	1011	Reserved
0100	4:1	1100	12:1
0101	5:1	1101	Reserved
0110	6:1	1110	Reserved
0111	Reserved	1111	Reserved

Table	60.	ССВ	Clock	Ratio
	•••			

19.3 e500 Core PLL Ratio

Table 61 describes the clock ratio between the e500 core complex bus (CCB) and the e500 core clock. This ratio is determined by the binary value of LBCTL, LALE, and LGPL2 at power up, as shown in Table 61.

Table 61. e500 Core to CCB Clock Ratio
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Binary Value of LBCTL, LALE, LGPL2 Signals	e500 core:CCB Clock Ratio	Binary Value of LBCTL, LALE, LGPL2 Signals	e500 core:CCB Clock Ratio
000	4:1	100	2:1
001	Reserved	101	5:2
010	Reserved	110	3:1
011	3:2	111	7:2

19.4 PCI Clocks

For specifications on the PCI_CLK, refer to the PCI 2.2 Local Bus Specifications.

The use of PCI_CLK is optional if SYSCLK is in the range of 33–66 MHz. If SYSCLK is outside this range then use of PCI_CLK is required as a separate PCI clock source, asynchronous with respect to SYSCLK.





20.3.4 Temperature Diode

The MPC8533E has a temperature diode on the microprocessor that can be used in conjunction with other system temperature monitoring devices (such as Analog Devices, ADT7461TM). These devices use the negative temperature coefficient of a diode operated at a constant current to determine the temperature of the microprocessor and its environment. It is recommended that each device be individually calibrated.

The following are voltage forward biased range of the on-board temperature diode:

$$V_{f} > 0.40 V$$

 $V_{f} < 0.90 V$

An approximate value of the ideality may be obtained by calibrating the device near the expected operating temperature. The ideality factor is defined as the deviation from the ideal diode equation:

$$I_{fw} = \mathbf{I}_{\mathbf{s}} \left[e^{\frac{\mathbf{q} \mathbf{V}_{f}}{\mathbf{n} \mathbf{K} \mathbf{T}}} - \mathbf{1} \right]$$

Another useful equation is:

$$\mathbf{V}_{\mathrm{H}} - \mathbf{V}_{\mathrm{L}} = \mathbf{n} \frac{\mathrm{KT}}{\mathrm{q}} \left[\mathbf{n} \frac{\mathrm{I}_{\mathrm{H}}}{\mathrm{I}_{\mathrm{L}}} \right]$$

Thermal